

## NCE P-Channel Enhancement Mode Power MOSFET

# **Description**

The NCE3407D uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , This device is suitable for use as a load switch or in PWM applications.

#### **General Features**

•  $V_{DS} = -30V, I_{D} = -3.9A$ 

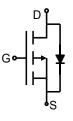
 $R_{DS(ON)}$  = 38m $\Omega$  @  $V_{GS}$ =-10V

 $R_{DS(ON)} = 62m\Omega$  @  $V_{GS}$ =-4.5V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

# **Application**

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

# **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3407D <sup>®</sup> X	NCE3407D	SOT-23	Ø180mm	8 mm	3000 units

# Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

—	,		
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	-3.9	А
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	-15.6	А
Maximum Power Dissipation	P <sub>D</sub>	1.4	W
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	°C

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	Reja	89	°C/W	

## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250µA	-30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V,V <sub>GS</sub> =0V	-	-	-1	μA



# http://www.ncepower.com

# NCE3407D

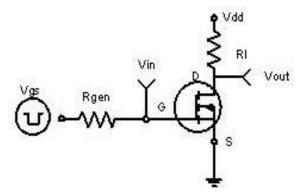
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-1.1	-1.6	-2.5	V
Danier Course On Otata Basistana	Б	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A	-	38	46	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	-	62	80	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-3A	-	10	-	S
Dynamic Characteristics (Note4)			'			
Input Capacitance	Clss	)/ 45\/\/ 0\/	-	523	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V, F=1.0MHz	-	78	-	PF
Reverse Transfer Capacitance	Crss	F=1.UMHZ	-	61	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	8.5	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =-15V, $R_L$ =5 $\Omega$	-	5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V, $R_{GEN}$ =3 $\Omega$	-	26	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	13	-	nS
Total Gate Charge	Qg		-	11.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V,I <sub>D</sub> =-3A,V <sub>GS</sub> =-10V	-	2.8	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	1.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-3A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-3.9	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> =-3A	-	11.2	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	5.5	-	nC

#### Notes:

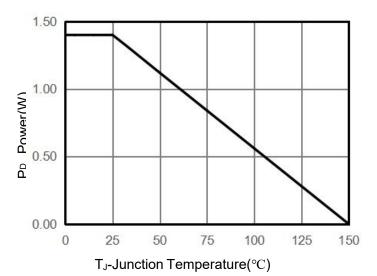
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2\%$ .
- 4. Guaranteed by design, not subject to production



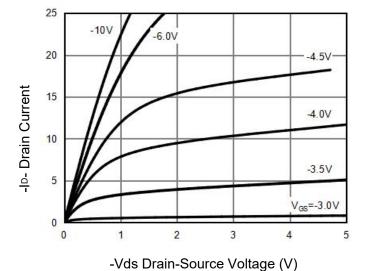
# **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 

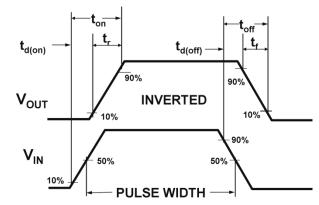


Figure 2:Switching Waveforms

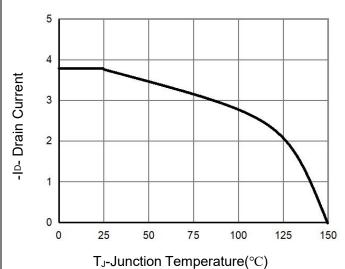


Figure 4 Drain Current

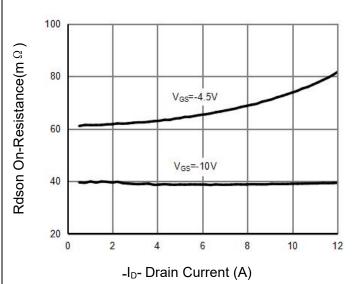


Figure 6 Drain-Source On-Resistance



Rdson On-Resistance(m  $\Omega$  )

-Vgs Gate-Source Voltage

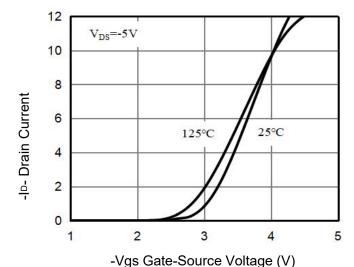
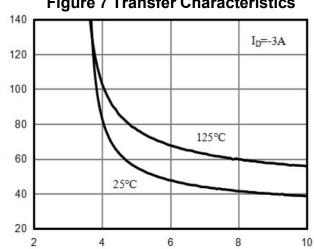


Figure 7 Transfer Characteristics



-Vgs Gate-Source Voltage (V)

# Figure 9 Rdson vs Vgs

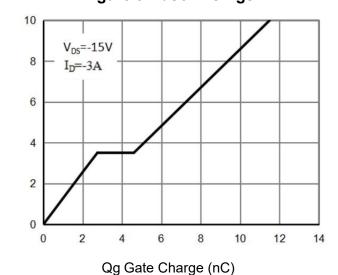
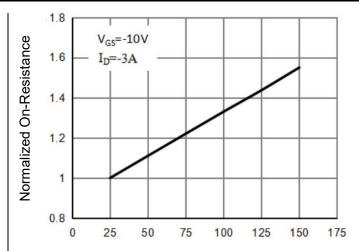
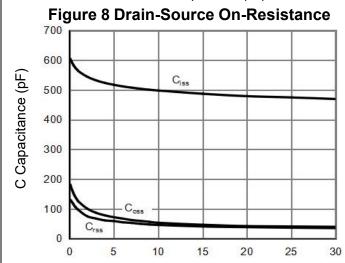


Figure 11 Gate Charge



T<sub>J</sub>-Junction Temperature(°C)



-Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

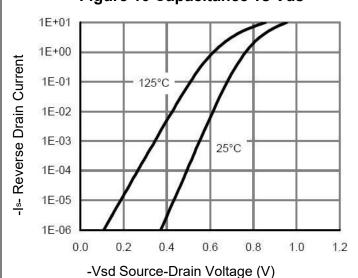
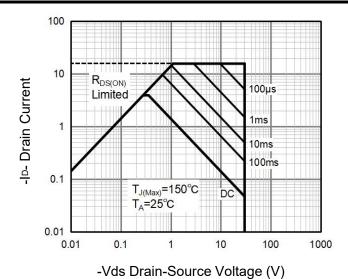
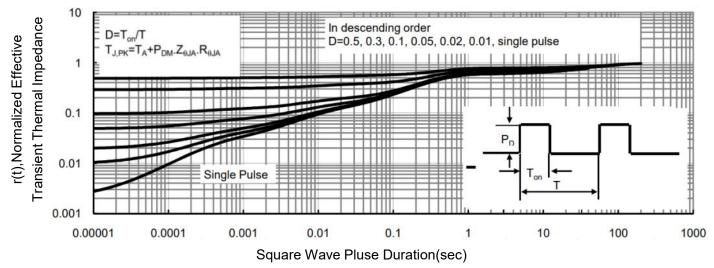


Figure 12 Source- Drain Diode Forward





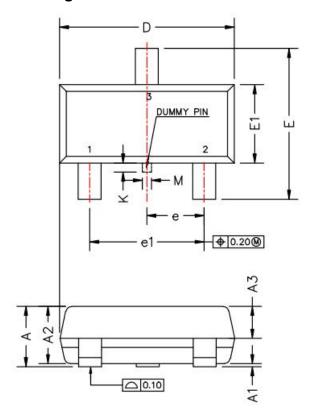
**Figure 13 Safe Operation Area** 

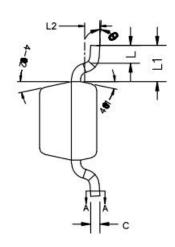


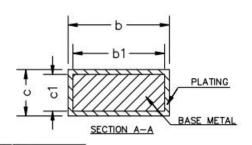
**Figure 15 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23 Package Information**







Cumbal	Millimeters			
Symbol	Min.	Max.		
Α	0.89 1.			
A1	0.01 0.1			
A2	0.88	1.02		
A3	0.43	0.63		
b	0.36	0.50		
b1	0.35	0.45		
С	0.14	0.20		
c1	0.14	0.16		
D	2.80	3.00		
E	2.35	2.64		
E1	1.20	1.40		
е	0.90	1.00		
e1	1.80	2.00		
L	0.40	0.60		
L1	0.6REF			
L2	0.25BSC			
θ	0°	8°		
01	10°	14°		
θ2	10°	14°		



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